



# **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - :  $V_{CEO(SUS)} = 300V(Min)$
- · High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

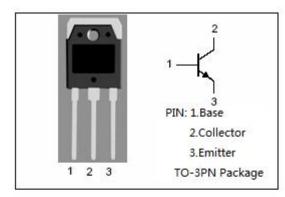
• Designed for use in converters, inverters, switchingregulators, motor control systems etc.

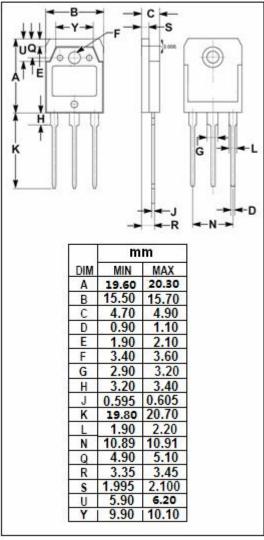
# ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CES</sub>	Collector- Emitter Voltage V <sub>BE</sub> =0	550	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	300	V	
V <sub>EBO</sub>	Emitter-Base Voltage	9	V	
Ic	Collector Current-Continuous 8		Α	
Ісм	Collector Current-Peak	20	Α	
lв	Base Current-Continuous	4	Α	
Івм	Base Current-Peak	6	Α	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25 °C	125	W	
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$	

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.0	°C/W







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**BUP22** 

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ;I <sub>B</sub> = 0	300			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 0.67A			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 0.67A			1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = V <sub>CESmax</sub> ;V <sub>BE</sub> = 0 V <sub>CE</sub> = V <sub>CESmax</sub> ;V <sub>BE</sub> = 0; T <sub>J</sub> = 125°C			1 2	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 9V; I <sub>C</sub> =0			10	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		25		
Switching Times; Resistive Load						

ton	Turn-On Time	I <sub>C</sub> = 6A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.67A	0.5	μς
ts	Storage Time		3.0	μ \$
tf	Fall Time		0.3	μS

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